

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): M.A. Shibib et al.
Case: 41-10
Serial No.: To Be Assigned
Filing Date: November 21, 2003
Group: To Be Assigned
Examiner: To Be Assigned

Title: Metal-Oxide-Semiconductor Device
Formed in Silicon-On-Insulator

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. §§1.56, 1.97 and 1.98, Applicants' attorney wishes to bring to the attention of the Patent and Trademark Office the following documents listed on the accompanying Form PTO-1449. A copy of each listed document is enclosed, other than the published U.S. patent document.

U.S. Patent Documents

1. U.S. Patent No. 6,461,902 issued on 10/08/02 to Xu et al.

Other Documents

1. J. Cai et al., "A Partial SOI Technology for Single-Chip RF Power Amplifiers," IEEE, pp. 40.3.1-40.3.4, 2001.
2. S. Matsumoto et al., "A Quasi-SOI Power MOSFET for Radio Frequency Applications Formed by Reversed Silicon Wafer Direct Bonding," IEEE, pp. 1448-1453, 2001.

The filing of this Information Disclosure Statement shall not be construed as a representation that a search has been made, or as an admission that the information cited is considered to be material to patentability, or as a representation that no other material information exists.

Respectfully submitted,

A handwritten signature in black ink, appearing to read "Wayne L. Ellenbogen", with a long, sweeping horizontal line extending to the right.

Date: November 21, 2003

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FORM PTO-1449 (MODIFIED)**LIST OF PUBLICATIONS FOR
APPLICANT'S INFORMATION
DISCLOSURE STATEMENT**

Applicant(s): M.A. Shbib et al.
Case: 41-10
Serial No.: TBA
Filing Date: November 21, 2003
Group: TBA

U.S. PATENT DOCUMENTS

| EXAMINER | | | | FILING DATE |
|----------|--------------|------|------|----------------|
| INITIAL | DOCUMENT NO. | DATE | NAME | IF APPROPRIATE |

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|----|-----------|----------|-----------|--|
| 1. | 6,461,902 | 10/08/02 | Xu et al. | |
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FOREIGN PATENT DOCUMENTS

| EXAMINER | | | | TRANSLATION | |
|----------|--------------|------|---------|----------------|--------|
| INITIAL | DOCUMENT NO. | DATE | COUNTRY | CLASS/SUBCLASS | YES NO |

OTHER DOCUMENTS

| EXAMINER | | |
|----------|---------|--|
| INITIAL | REF NO. | AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC. |

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| 1. | J. Cai et al., "A Partial SOI Technology for Single-Chip RF Power Amplifiers," IEEE, pp. 40.3.1-40.3.4, 2001. |
| 2. | S. Matsumoto et al., "A Quasi-SOI Power MOSFET for Radio Frequency Applications Formed by Reversed Silicon Wafer Direct Bonding," IEEE, pp. 1448-1453, 2001. |

Examiner

Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.